UNISONIC TECHNOLOGIES CO., LTD

UTG75N65-S

Preliminary

Insulated Gate Bipolar Transistor

650V TRENCH GATE FIELD-STOP IGBT

DESCRIPTION

The UTC **UTG75N65-S** is an Trench Field-Stop Insulated Gate Bipolar Transistor. it uses UTC's advanced technology to provide customers with high switching speed, low saturation voltage and low switching loss, etc.

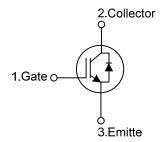
The UTC **UTG75N65-S** is suitable for the resonant or soft switching applications.

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■ FEATURES

- * High switching speed
- * High avalanche ruggedness
- * Low saturation voltage: $V_{CE(SAT).Typ.}$ =1.65V @ I_C=75A, V_{GE} =15V (T_C =25°C)

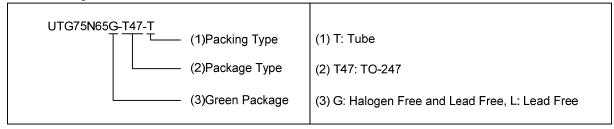
■ SYMBOL



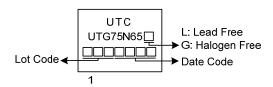
■ ORDERING INFORMATION

Ordering Number		Deeleene	Pin	Assignm	Da alda a		
Lead Free	Halogen Free	Package	1	2	3	Packing	
UTG75N65L-T47-T	UTG75N65G-T47-T	TO-247	G	С	Е	Tube	

Note: Pin Assignment: G: Gate C: Collector E: Emitter



■ MARKING



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■ **ABSOLUTE MAXIMUM RATINGS** (T_A=25°C, unless otherwise noted)

PARAMETER		SYMBOL	RATINGS	UNIT	
Collector-Emitter Voltage		V _{CES}	650	V	
Gate-Emitter Voltage		\ /	±20	V	
Transient Gate-emitter voltage (tp < 5 ms)		V_{GES}	±25	V	
Continuous Collector Current	T _C =25°C	Ic	150	Α	
	T _C =100°C		75	Α	
Collector Current Pulsed (Note 1)		I _{CM}	300	Α	
Diada Famuand Cumant	T _C =25°C	I _F	150	Α	
Diode Forward Current	T _C =100°C		75	Α	
Short Circuit Withstand Time $V_{GE} = 15V$, $V_{CC} \le 200V$ Allowed number of short circuits < 1000 Time between short circuits: $\ge 1.0s$ $T_{VJ} = 25^{\circ}C$		tsc			
				μs	
			3		
			Power Dissipation (T _C =25°C)		P _D
Operating Junction Temperature		T_J	-40 ~ +175	°C	
Storage Temperature Range		T _{STG}	-55 ~ +175	°C	

Notes: 1. Absolute maximum ratings are stress ratings only and functional device operation is not implied. Absolute maximum ratings are those values beyond which the device could be permanently damaged.

■ THERMAL DATA

PARAMETER	SYMBOL	RATING	UNIT
Junction to Case	θјς	0.4	°C/W

^{2.} Pulse width limited by maximum junction temperature.

ELECTRICAL CHARACTERISTICS (T_C=25°C, unless otherwise noted)

	PARAMETER SYMBOL TEST CONDITIONS		IONS	MIN	TYP	MAX	UNIT
Off Characteristics	I	1			1	1	
Collector-Emitter Breakdown Voltage	BV _{CES}			650			V
Collector Cut-Off Current	I _{CES}	V _{CE} =650V, V _{GE} =0V				5	μΑ
G-E Leakage Current	I _{GES}	V _{CE} =0V, V _{GE} =±20V				±400	nA
On Characteristics							
Gate to Emitter Threshold Voltage	$V_{GE(TH)}$	I _C =250μA, V _{CE} =V _{GE}		4.5		6.5	٧
Collector to Emitter Saturation Voltage	V _{CE(SAT)}	I _C =75A, V _{GE} =15V	T _C =25°C		1.65	2.1	٧
	- 02(0/11)		T _C =125°C		2.0		V
Dynamic Characteristics	1	<u>†</u>			1		
Input Capacitance	C _{IES}	V _{CE} =25V, V _{GE} =0V, f=1MHz			4240		pF
Output Capacitance	C _{OES}				340		pF
Reverse Transfer Capacitance	C _{RES}				59.5		pF
Switching Characteristics				_			
Total Gate Charge	Q_{G}	V _{CE} =520V, I _C =75A, V _{GE} =15V			219		nC
Gate-Emitter Charge	Q_{GE}				93		nC
Gate-Collector Charge	Q _{GC}				71		nC
Turn-On Delay Time	t _{DON)}				28		ns
Rise Time	t _R				80		ns
Turn-Off Delay Time	t _{DOFF)}	V _{CC} =400V, I _C =75A, R _G =10Ω, V _{GE} =0~15V, L=100uH			155		ns
Fall Time	t _F				51		ns
Turn-On Switching Loss	Eon				2.43		mJ
Turn-Off Switching Loss	E _{OFF}			1.87		mJ	
SOURCE- DRAIN DIODE RATINGS AN	D CHARACTE	RISTICS					
Forward Voltage Drop	VF	I _F =75A				3.0	V
Reverse Recovery Time	t _{rr}	I _F =75A, dl/dt=100A/μS, V _{CC} =400V			43.3		ns
Reverse Recovery Charge	Qrr				472.8		nC
•	Qrr				472.8		nC

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